

Basics and Op-Amps

(Thevenin voltage) $V_{TH} = V_{OC}$

(Norton current) $I_N = I_{SC}$

(Equivalent impedance) $R_{eq} = Z_{eq} = \frac{V_{OC}}{I_{SC}}$

(Equivalent admittance) $Y_{eq} = \frac{I_{SC}}{V_{OC}}$

(Parallel R+L/series C) $x_{eq} = \frac{AB}{A+B}$

(Root-mean-square of sine) $V_{rms} = \sqrt{2}V_{max}$

Op-Amps

Typical Op-Amp Filters	
<p>Inverting Amp</p> <p>$V_{out} = -\frac{R_2}{R_1} V_{in}$</p>	<p>Summing Amp</p> <p>$V_{out} = -\left(\frac{R_F}{R_1} V_1 + \frac{R_F}{R_2} V_2\right)$</p>
<p>Integrating Amp</p> <p>$V_{out} = -\frac{1}{RC} \int V_{in}$</p>	<p>Differentiating Amp</p> <p>$V_{out} = -RC \frac{dV_{in}}{dt}$</p>
<p>Non-Inverting Amp</p> <p>$V_{out} = \frac{R_1 + R_2}{R_2} V_{in}$</p>	<p>Differencing Amp</p> <p>$V_{out} = -\frac{R_2}{R_1} V_1 + \frac{R_1 + R_2}{R_1} \frac{R_4}{R_3 + R_4} V_2$</p>

Ideally, $Z_{in} = A_{OC} = CMR = GBWP = \infty$, $Z_{out} = SR = 0$

(Diff. gain) $A_d = \frac{R_2}{R_1}$ given $\frac{R_4}{R_3} = \frac{R_2}{R_1}$

(Diff. out) $V_{out} = \Delta V A_d + |V| A_{cm}$

(Common mode rejection rate) $CMRR = 20 \log \frac{|A_d|}{|A_{cm}|}$

(Max frequency for slew rate on sin input) $f_m = \frac{SR}{2\pi V_{max}}$

(Freq affects amp gain) $GBWP = f_{3dB} A$

Offset voltage Voltage source V_{OS} connected in series between port and terminal of ideal op-amp.

Input Bias/Offset Current 2 current sources $I_{Bn} = I_B \pm 5I_{OS}$ connected in parallel between port and terminal going to ground.

Semiconductors

$q = 1.602 \times 10^{-19} \text{ C}$

$\epsilon_s = 11.7\epsilon_0 = 1.04 \times 10^{-12} \frac{\text{F}}{\text{cm}}$

$n = p = n_i = BT^{\frac{3}{2}} e^{\frac{-E_g}{2kT}}$

$B_{Si} = 7.3 \times 10^{15} \text{ cm}^{-3} \text{ K}^{-\frac{3}{2}}$

$E_{gSi} = 1.12 \text{ eV}$

$k = 8.62 \times 10^{-5} \frac{\text{eV}}{\text{K}}$

For $N_D \gg n_i$, $n_n \approx N_D$, $p_n = \frac{n_i^2}{n_n} \approx \frac{n_i^2}{N_D}$

For $N_A \gg n_i$, $p_p \approx N_A$, $n_p = \frac{n_i^2}{p_p} \approx \frac{n_i^2}{N_A}$

(Built-in voltage) $V_0 = \frac{kT}{q} \ln \left(\frac{N_A N_D}{n_i^2} \right)$

(Depletion region width) $W = \sqrt{\frac{2\epsilon_s}{q} \left(\frac{1}{N_A} + \frac{1}{N_D} \right) (V_0 + V_R)}$

$x_p = W \frac{N_D}{N_A + N_D}$ $x_n = W \frac{N_A}{N_A + N_D}$

(Junction charge) $Q_J = Aq \left(\frac{N_A N_D}{N_A + N_D} \right) W$

$\mu_{pSi} = 480 \frac{\text{cm}^2}{\text{Vs}}$ $\mu_{nSi} = 1350 \frac{\text{cm}^2}{\text{Vs}}$

$C_{ox} = \epsilon_{ox} T_{ox}$

Diodes

Ideal diodes are an open circuit when the voltage across them is negative (reverse bias), or a short circuit when the voltage across them is positive (forward bias).

Constant voltage drop is a very similar model that goes to a short circuit at some forward voltage v_D , which is dropped across the diode once it turns on.

Zener diodes are used "backwards", so they can operate in the breakdown region. $V_Z = V_{Z0} + r_Z I_Z$

Rectifiers

(Half-wave) $PIV = V_s$

(Half-wave) $V_o = v_s - v_D$ for $v_s \geq v_D$

(Full-wave) $PIV = 2V_s - V_D$

(Full-wave) $V_o = |v_s| - v_D$ for $|v_s| \geq v_D$

(Bridge) $PIV = V_s - V_d$

(Bridge) $V_o = |v_s| - 2v_D$ for $|v_s| \geq 2v_D$

(Half-wave Peak) $i_{D_{av}} = I_L (1 + \pi \sqrt{2V_p/V_r})$

(Half-wave Peak) $i_{D_{max}} = I_L (1 + 2\pi \sqrt{2V_p/V_r})$

(Half-wave Peak) $V_r = \frac{V_p}{fCR}$

For full-wave peak, replace $\sqrt{2V_p/V_r}$ with $\sqrt{V_p/2V_r}$ and $V_r = \frac{V_p}{fCR}$ with $V_r = \frac{V_p}{2fCR}$.

Transistors

(Overdrive voltage) $V_{OV} \equiv v_{GS} - V_t$

n-channel

p-channel MOSFETs have the source (arrow) on bottom or the body arrow (if the body is not connected to the source) pointing in toward the circuit symbol.

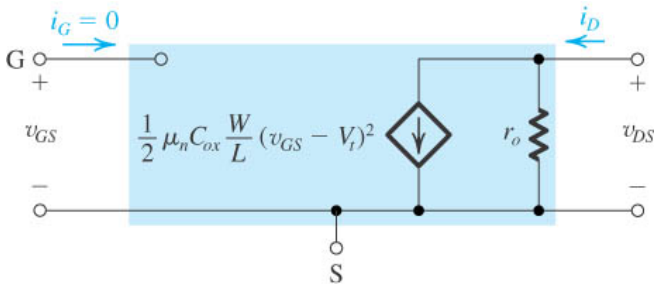
(Transconductance) $k_n = \mu_n C_{ox} W/L = k'_n W/L$

(Small-signal R) $r_{DS} = ((\mu_n C_{ox})(W/L)(v_{GS} - v_t))^{-1}$

(Cutoff) $i_D = 0 \quad v_{GS} \leq V_t$

(Triode) $i_D = k_n (V_{OV} - \frac{1}{2}v_{DS}) v_{DS} \quad v_{DS} < V_{OV}$

(Saturation) $i_D = \frac{1}{2}k_n V_{OV}^2 (1 + \lambda v_{DS}) \quad v_{DS} \geq V_{OV}$



p-channel

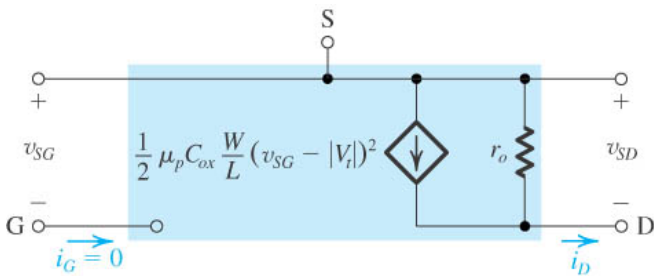
p-channel MOSFETs have the source (arrow) on top or the body arrow (if the body is not connected to the source) pointing out from the circuit symbol.

(Transconductance) $k_p = \mu_p C_{ox} W/L = k'_p W/L$

(Cutoff) $i_D = 0 \quad v_{SG} \leq |V_t|$

(Triode) $i_D = k_p (|V_{OV}| - \frac{1}{2}v_{SD}) v_{SD} \quad v_{SD} < |V_{OV}|$

(Saturation) $i_D = \frac{1}{2}k_p |V_{OV}|^2 (1 + |\lambda|v_{SD}) \quad v_{SD} \geq |V_{OV}|$



Small-Signal MOSFETs

$$g_m = \frac{dI_{DS}}{dV_{GS}} = k_n V_{OV} = \frac{2I_D}{V_{OV}}$$

(Early voltage) $\lambda = 1/V_A \quad r_o = \frac{V_A}{I_D}$

MOSFET Amps

$$R_{in} = \infty \text{ for all but CG, where } R_{in} = \frac{1}{g_m}$$

$$R_o = R_D \text{ for all but SF, where } R_o = \frac{1}{g_m}$$

Amp	A_{vo}	A_v	G_v
CS	$-g_m R_D$	$-g_m (R_D R_L)$	$-g_m (R_D R_L)$
CS+R	$-\frac{g_m R_D}{1 + g_m R_s}$	$-\frac{g_m (R_D R_L)}{1 + g_m R_s}$	$-\frac{g_m (R_D R_L)}{1 + g_m R_s}$
CG	$g_m R_D$	$g_m (R_D R_L)$	$-\frac{R_D R_L}{R_{sig} + g_m^{-1}}$
SF	1	$\frac{R_L}{R_L + g_m^{-1}}$	$-\frac{R_L}{R_{sig} + g_m^{-1}}$

MOSFET current source

Connect MOSFETs gate to gate to get a current source/mirror:

$$\frac{I_{ref}}{W/L} = \frac{I_{D1}}{(W/L)_1} = \frac{I_{D2}}{(W/L)_2} = \dots$$

Finding Frequency Response

- Assume saturation and find I_D , V_{GS} , V_{DS} for the bias point (Q-point), then ensure that the assumption is correct
- Use Q-point to estimate g_m , r_o
- Short DC voltages, coupling/bypass caps, open DC currents; analyze for A_v , R_{in} , R_{out} ; estimate G_v

T model

